

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
S1	1745	438/694	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/04 07:19
S2	1	10/718070	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/04 15:57
S3	67105	phase near change	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/04 13:36
S8	47546	IBM.as.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/03 07:36
S9	46	S3 and S8	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/03 07:41
S12	137037	memory near cell	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/03 07:44
S18	14149	multiple near bit	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/03 07:45
S19	15909	multi-bit	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/03 07:45
S20	28058	S18 or S19	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/03 07:45
S21	139	S8 and S20	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/03 07:46

S22	7	S12 and S21	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/03 08:41
S24	2	"6180456".pn.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/03 08:44
S25	163	(crystallize or crystallization) near (temperature or heat)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/03 08:53
S27	2	nitrogen near (doping or dope) near resistivity	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/03 08:53
S28	22	S25 and memory	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/03 08:58
S29	123	Ge2Sb2Te5	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/03 12:06
S30	1717773	memory	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/03 08:58
S31	6622135	TiN Ti TiW W Ta TaN Al Cu Pt	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/03 08:59
S32	73	TiN Ti TiW W Ta TaN Al Cu Pt	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2005/10/03 09:00
S33	33	S30 and S32	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2005/10/03 09:00

S34	1	S33 and S29	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2005/10/03 09:01
S35	49290	phase adj change or (phase-change)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2005/10/03 09:02
S36	8	S33 and S35	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2005/10/03 09:02
S37	1	S34 and S36	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2005/10/03 09:22
S38	185066	multilayer	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2005/10/03 09:22
S39	168458	phase near (change or shift)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2005/10/03 09:23
S40	47	S38 near S39	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2005/10/03 10:01
S41	3	S40 and spacer	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2005/10/03 10:01
S42	6	resistance near phase near change near layer	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/03 11:15
S43	6285	(phase near change near material)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/03 11:16

S44	11658	(different near (resistance or resistivity))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/03 11:16
S45	6	S43 near S44	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/03 11:30
S46	6	10/384994	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/03 11:46
S47	3	10/657285	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/03 11:46
S48	2	"6087674".pn.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/03 12:03
S49	0	Ge2Sb2Te5 and cognegen	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/03 12:06
S50	1	Ge2Sb2Te5 and chalcogen	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/03 12:06
S51	6	10/384994	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/03 12:49
S52	3596000	many or multi or multiple	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/04 17:02
S53	3480365	layer	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/03 12:50

S54	49290	phase adj change	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/03 12:50
S55	6413419	material	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/03 12:50
S56	17563	GST	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/03 12:50
S57	177133	S52 near S53	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/03 12:50
S58	6013	S54 near S55	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/03 12:51
S59	1	10/796479	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/03 17:47
S60	17	"6573199"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/03 17:47
S61	0	"6573199.pn."	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/03 17:47
S62	2	"6573199".pn.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/03 17:47
S63	2869	(metal adj oxide) and tantalum and pentoxide and aluminum pentoxide and hafnium oxide and (titanium adj oxide) and (silicon adj oxynitride)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/04 07:21

S64	3	(metal adj oxide) near (tantalum and pentoxide and aluminum pentoxide and hafnium oxide and (titanium adj oxide) and (silicon adj oxynitride))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/04 07:23
S65	3932	(tantalum and pentoxide and aluminum pentoxide and hafnium oxide and (titanium adj oxide) and (silicon adj oxynitride))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/04 07:23
S66	0	(tantalum and pentoxide and (aluminum adj pentoxide) and (hafnium adj oxide) and (titanium adj oxide) and (silicon adj oxynitride))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/04 07:23
S67	29	(tantalum and pentoxide and (hafnium adj oxide) and (titanium adj oxide) and (silicon adj oxynitride))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/04 08:24
S69	2	"2005079473"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/04 09:42
S70	28	plasma near treatment near nitride	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/04 09:48
S71	16	oxygen near plasma near nitride	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/04 09:53
S72	2	"5714037".pn.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/04 09:53
S73	4681880	multiple or several or many or multi	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/04 10:37
S74	1680	phase near change near layers	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/04 10:37

S75	24	S73 near S74	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/04 13:10
S76	2	"5536947".pn.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/04 14:42
S77	1027	"same" near resistivity	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/04 13:35
S78	67146	phase near change	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/04 14:51
S79	0	S78 near S77	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/04 13:36
S80	23	"same" near phase near transition near temperature	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/04 14:45
S81	6426	phase near transition near temperature	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/04 14:46
S82	6031	phase adj transition adj temperature	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/04 14:46
S83	67146	phase near change	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/04 14:46
S84	693	S82 and S83	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/04 14:46

S85	207	S82 same S83	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/04 14:46
S86	51	S82 near S83	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/04 14:46
S87	3581281	temperature	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/04 14:51
S88	2148	S87 near S83	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/04 14:51
S89	0	"6,087,674,pn."	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/04 14:57
S90	2	"6,087,674".pn.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/04 14:57
S91	6	10/384994	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/04 15:43
S92	1043	inner near conductive adj layers	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/04 15:57
S93	31	S92 and S83	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/04 15:58
S94	28	S93 and memory	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/04 15:59

S95	853	phase adj change adj memory	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/04 15:59
S98	294	OUM	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/04 16:00
S99	34834	PCM	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/04 16:00
S100	35636	S99 or S95	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/04 16:00
S101	33	S100 and S98	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/04 16:01
S102	0	conductoy near layel	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/04 16:01
S103	38497	conductor near layer	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/04 16:01
S104	35897	S100 or S98	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/04 16:01
S105	63	S103 and S104	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/04 16:01
S106	2379294	inner	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/04 16:02

S10 7	8	S105 and S106	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/04 16:04
S10 8	18027	inner near conductor	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/04 16:05
S10 9	45412	control near electrode	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/04 16:06
S11 0	103	S104 and S109	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/04 16:07
S11 1	402	S95.ab.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/04 16:07
S11 2	351	S95.ti.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/04 16:45
S11 3	49	"same" near transition adj temperature	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/04 16:46
S11 4	50	"same" near transition near temperature	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/04 16:46
S11 5	0	S114 and S101	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/04 17:02
S11 6	49319	(phase adj change)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/04 17:02

S11 7	7803	"52" near materials	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/04 17:03
S11 8	12	S116 near S117	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/04 17:03
S11 9	3581281	temperature	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/04 17:03
S12 0	11	S118 and S119	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/04 17:03
S12 1	5197541	"same"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/04 17:03
S12 2	11	S120 and S121	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/04 17:05
S12 3	5	(phase adj change) near (different adj materials)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/04 17:05